



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	I _D max T _A = +25°C
00)/	$16m\Omega$ @ $V_{GS} = 10V$	9.8A
30V	$23m\Omega$ @ $V_{GS} = 4.5V$	8.7A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features

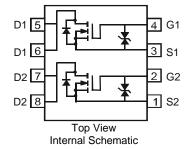
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)







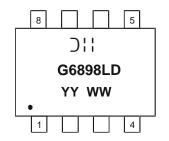
Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging
DMG6898LSD-13	Commercial	SO-8	2,500 / Tape & Reel
DMG6898LSDQ-13	Automotive	SO-8	2,500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



O':: = Manufacturer's Marking G6898LD = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 14 = 2014) WW = Week (01 - 53)



Maximum Ratings @T_A = +25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	9.5 7.1	А
Pulsed Drain Current (Note 7)			I _{DM}	30	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	1.28	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	$R_{\theta JA}$	99.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

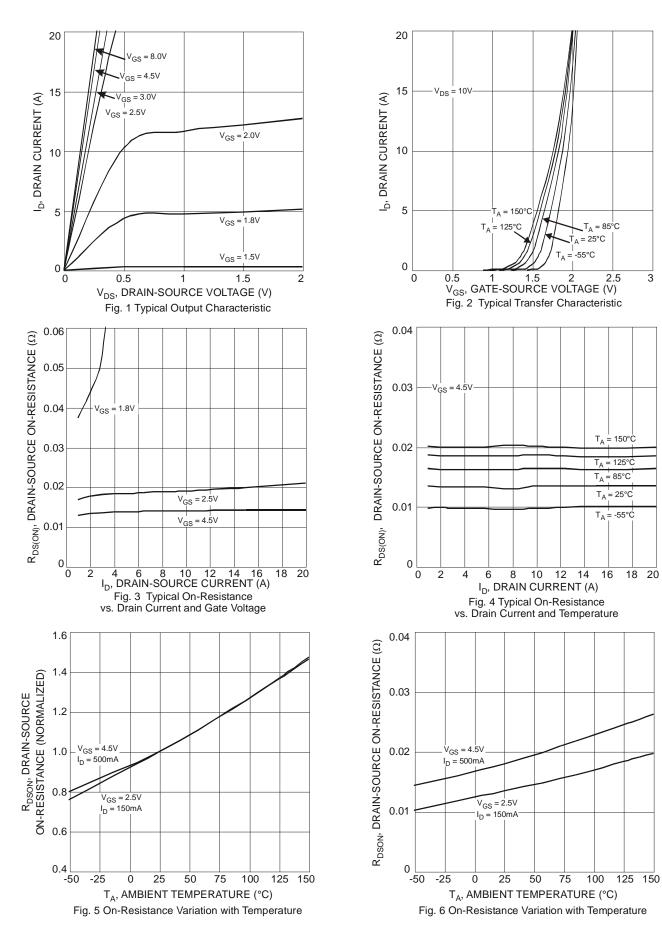
Electrical Characteristics @T_A = +25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	0.5	1.0	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			11	16	mΩ	$V_{GS} = 4.5V, I_D = 9.4A$	
Static Dialif-Source On-Nesistance	R _{DS} (ON)	-	17	23	11177	$V_{GS} = 2.5V, I_D = 8.3A$	
Forward Transfer Admittance	Y _{fs}	-	17	-	S	$V_{DS} = 5V, I_{D} = 9.4A$	
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.3A$	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C _{iss}	-	1149	-	pF		
Output Capacitance	Coss	-	157	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	142	-	pF	71 = 1.01VIMZ	
Gate Resistance	Rg	-	1.51	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	11.6	-	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	-	26	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 9.4A$	
Gate-Source Charge	Q _{gs}	-	2.7	-	nC		
Gate-Drain Charge	Q_{gd}	-	3.4	-	nC		
Turn-On Delay Time	t _{D(on)}	-	11.67	-	ns		
Turn-On Rise Time	t _r	-	12.49	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	35.89	-	ns	$R_{GEN} = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _f	-	12.33	-	ns	1	

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 7. Repetitive rating, pulse width limited by junction temperature.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.







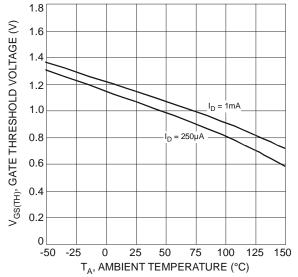
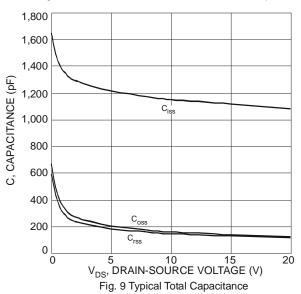
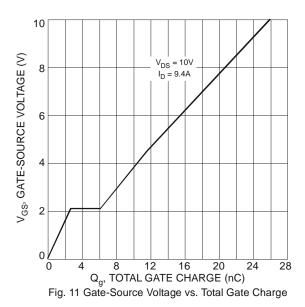


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





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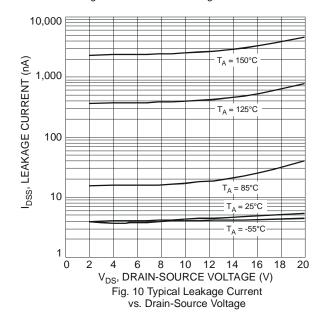
(v) 15

(v) 15

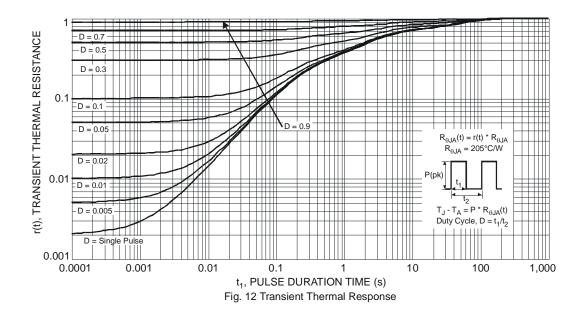
(v) 15

(v) 10

(v

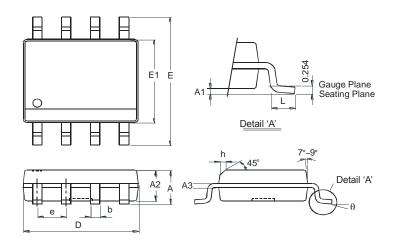






Package Outline Dimensions

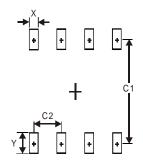
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
А3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90 6.			
E1	3.85	3.95		
е	1.27 Typ			
h		0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Υ	1.55
C1	5.4
C2	1.27



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